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Peter M. Smowton
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Contents

xi *Conference Committee*

LOW DIMENSIONAL MATERIALS

7953 02 **Quantum dot composite light sources** [7953-01]
D. W. Grund, Jr., B. C. Olbricht, D. W. Prather, Univ. of Delaware (United States)

7953 03 **Gain and absorption characteristics of bilayer quantum dot lasers beyond 1.3 µm** [7953-02]
M. A. Majid, S. C. Chen, D. T. D. Childs, H. Shahid, R. J. Airey, K. Kennedy, R. A. Hogg, The Univ. of Sheffield (United Kingdom); E. Clarke, P. Spencer, R. Murray, Imperial College London (United Kingdom)

7953 04 **Nanopatterned quantum dot active region lasers on InP substrates (Invited Paper)** [7953-03]
L. J. Mawst, J. H. Park, Y. Huang, J. Kirch, Univ. of Wisconsin-Madison (United States); Y. Sin, B. Foran, The Aerospace Corp. (United States); C.-C. Liu, P. F. Nealey, T. F. Kuech, Univ. of Wisconsin-Madison (United States)

7953 06 **The lateral ambipolar diffusion length in quantum dot lasers** [7953-05]
A. Sobiesierski, D. Naidu, P. M. Smowton, Cardiff Univ. (United Kingdom)

GRATING COUPLED

7953 08 **Deep etched distributed Bragg reflector (DBR) InP/AlGaInP quantum dot lasers** [7953-07]
S. Shutts, G. Edwards, S. N. Elliott, P. M. Smowton, Cardiff Univ. (United Kingdom); A. B. Krysa, The Univ. of Sheffield (United Kingdom)

7953 09 **Design and device characteristics of index-coupled wafer-level holographically patterned 1.3µm quantum dot distributed feedback lasers** [7953-08]
J. Hu, D. Klotzkin, Binghamton Univ. (United States); J. S. Huang, Emcore Broadband (United States); X. Sun, N. Li, Emcore (United States)

7953 0A **High power distributed feedback and Fabry-Perot Al-free laser diodes at 780nm for rubidium pumping** [7953-09]
C. Cayron, M. Tran, Y. Robert, M. Lecomte, M. Calligaro, O. Parillaud, M. Garcia, M. Krakowski, Alcatel-Thales III-V Lab. (France)

7953 0B **Narrow-linewidth distributed feedback lasers with laterally coupled ridge-waveguide surface gratings fabricated using nanoimprint lithography** [7953-10]
M. Dumitrescu, J. Telkkälä, J. Karinen, J. Viheriälä, A. Laakso, K. Haring, M.-R. Viljanen, J. Paajaste, R. Koskinen, S. Suomalainen, J. Lyytikäinen, T. Leinonen, M. Pessa, Tampere Univ. of Technology (Finland)

TELECOM/DATACOM

7953 0D **Development of high-speed directly modulated DFB and DBR lasers with surface gratings** [7953-12]
M. Dumitrescu, J. Telkkälä, J. Karinen, J. Viheriälä, A. Laakso, Tampere Univ. of Technology (Finland); S. Afzal, J.-P. Reithmaier, Univ. of Kassel (Germany); M. Kamp, Julius-Maximilians-Univ. Würzburg (Germany); P. Melanen, P. Uusimaa, Modulight, Inc. (Finland); P. Bardella, M. Vallone, I. Montrosset, Politecnico di Torino (Italy); O. Parillaud, M. Krakowski, Alcatel Thales III-V Lab. (France); D. Gready, G. Eisenstein, Technion (Israel); G. Sek, Wroclaw Univ. of Technology (Poland)

7953 0E **1.55 µm directly modulated CCIG lasers fabricated by surface-defined lateral feedback gratings** [7953-13]
S. Afzal, F. Schnabel, W. Scholz, J.-P. Reithmaier, Univ. of Kassel (Germany); G. Eisenstein, D. Gready, Technion (Israel); O. Parillaud, M. Krakowski, Alcatel-Thales III-V Lab. (France); I. Montrosset, M. Vallone, Politecnico di Torino (Italy)

7953 0F **40 Gbit/s directly modulated lasers: physics and application (Invited Paper)** [7953-14]
U. Troppenz, J. Kreissl, M. Möhrle, C. Bornholdt, W. Rehbein, B. Sartorius, Fraunhofer Institute for Telecommunications (Germany); I. Woods, Cogo Optronics Inc. (United States); M. Schell, Fraunhofer Institute for Telecommunications (Germany)

NITRIDES

7953 0G **Recent results of blue and green InGaN laser diodes for laser projection (Invited Paper)** [7953-15]
S. Lutgen, D. Dini, I. Pietzonka, S. Tautz, A. Breidenassel, A. Lell, A. Avramescu, C. Eichler, T. Lermer, J. Müller, G. Bruederl, A. Gomez-Iglesias, U. Strauss, OSRAM Opto Semiconductors GmbH (Germany); W. G. Scheibenzuber, U. T. Schwarz, Fraunhofer IAF (Germany); B. Pasenow, S. Koch, Univ. Marburg (Germany)

7953 0H **Gain characteristics of deep UV AlGaN quantum wells lasers** [7953-16]
J. Zhang, H. Zhao, N. Tansu, Lehigh Univ. (United States)

7953 0I **Plasmonic cladding InGaN MQW laser diodes (Invited Paper)** [7953-17]
P. Perlin, K. Holc, M. Sarzyński, M. Leszczyński, R. Czernecki, Institute of High Pressure Physics (Poland) and TopGaN Ltd. (Poland); Ł. Marona, Institute of High Pressure Physics (Poland); P. Wisniewski, Institute of High Pressure Physics (Poland) and TopGaN Ltd. (Poland); G. Cywinski, C. Skierbiszewski, M. Bockowski, I. Grzegory, T. Suski, Institute of High Pressure Physics (Poland)

7953 0J **High peak power picoseconds optical pulse generation from GaInN semiconductor diode lasers (Invited Paper)** [7953-18]
R. Koda, Tohoku Univ. (Japan) and Sony Corp. (Japan); T. Oki, Sony Corp. (Japan); T. Miyajima, Tohoku. Univ. (Japan) and Sony Corp. (Japan); H. Watanabe, Sony Corp. (Japan); S. Kono, Tohoku Univ. (Japan); M. Kuramoto, M. Ikeda, Tohoku Univ. (Japan) and Sony Corp. (Japan); H. Yokoyama, Tohoku Univ. (Japan)

7953 0K **Dynamics of GaN-based laser diodes from violet to green** [7953-19]
W. G. Scheibenzuber, C. Hornuss, Fraunhofer IAF (Germany); U. T. Schwarz, Fraunhofer IAF (Germany) and Freiburg Univ. (Germany)

QUANTUM CASCADE LASERS I

7953 0N **The temperature dependence of key electro-optical characteristics for mid-infrared emitting quantum cascade lasers (Invited Paper)** [7953-22]
D. Botez, J. C. Shin, Univ. of Wisconsin-Madison (United States); S. Kumar, Lehigh Univ. (United States); J. Kirch, C.-C. Chang, L. J. Mawst, Univ. of Wisconsin-Madison (United States); I. Vurgaftman, J. R. Meyer, U.S. Naval Research Lab. (United States); A. Bismuto, B. Hinkov, J. Faist, ETH Zurich (Switzerland)

THz QUANTUM CASCADE LASERS I

7953 0O **High-temperature performance and broad continuous tunability of terahertz quantum-cascade lasers (Invited Paper)** [7953-23]
S. Kumar, Lehigh Univ. (United States); Q. Qin, C. W. I. Chan, Q. Hu, Massachusetts Institute of Technology (United States); J. L. Reno, Sandia National Labs. (United States)

7953 0P **Broadband semiconductor terahertz laser based on heterogeneous cascades** [7953-24]
D. Turčinková, G. Scalari, M. I. Amanti, F. Castellano, M. Beck, J. Lloyd-Hughes, J. Faist, ETH Zurich (Switzerland)

THz LASERS II

7953 0S **Monolithically integrated THz transceivers (Invited Paper)** [7953-27]
M. C. Wanke, M. Lee, C. D. Nordquist, M. J. Cich, Sandia National Labs. (United States); A. D. Grine, LMATA Government Services (United States); C. T. Fuller, J. L. Reno, Sandia National Labs. (United States)

7953 0T **Stimulated Smith-Purcell semiconductor THz sources** [7953-28]
D. D. Smith, A. Belyanin, Texas A&M Univ. (United States)

7953 0U **Upper limits on terahertz difference frequency generation power in quantum well heterostructures** [7953-29]
Y.-H. Cho, Texas A&M Univ. (United States); M. A. Belkin, The Univ. of Texas at Austin (United States); A. Belyanin, Texas A&M Univ. (United States)

HIGH POWER I

7953 0Z **670 nm nearly diffraction limited tapered lasers with more than 30% conversion efficiency and 1 W cw and 3 W pulsed output power** [7953-34]
B. Sumpf, P. Adamiec, M. Zorn, H. Wenzel, G. Erbert, G. Tränkle, Ferdinand-Braun-Institut für Höchstfrequenztechnik (Germany)

7953 10 **Versatile 1 W narrow band 976nm and 1064nm light sources** [7953-35]
S. Mohrdiek, H.-U. Pfeiffer, E. A. Zibik, B. Sverdlov, T. Pliska, N. Lichtenstein, Oclaro Switzerland AG (Switzerland)

7953 11 **1 W semiconductor based laser module with a narrow linewidth emitting near 1064 nm** [7953-36]
S. Spießberger, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany); M. Schiemangk, Humboldt-Univ. zu Berlin (Germany); A. Sahm, A. Wicht, H. Wenzel, J. Fricke, G. Erbert, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany)

MID-INFRARED LASERS

7953 14 **Room-temperature 4.0-μm broadened optical pumping injection cavity lasers** [7953-39]
L. J. Olafsen, Baylor Univ. (United States); L. E. Bain, Baylor Univ. (United States) and Univ. of North Carolina, Chapel Hill (United States); W. W. Bewley, I. Vurgaftman, J. R. Meyer, U.S. Naval Research Lab. (United States); H. Lee, Sarnoff Corp. (United States) and Applied Optoelectronics, Inc. (United States); R. U. Martinelli, Sarnoff Corp. (United States)

7953 15 **InGaAs/AlInAs quantum cascade laser sources based on intra-cavity second harmonic generation emitting in 2.6-3.6 micron range (Invited Paper)** [7953-40]
M. A. Belkin, M. Jang, R. W. Adams, The Univ. of Texas at Austin (United States); J. X. Chen, W. O. Charles, C. Gmachl, Princeton Univ. (United States); L. W. Cheng, F.-S. Choa, Univ. of Maryland, Baltimore County (United States); X. Wang, M. Troccoli, AdTech Optics, Inc. (United States); A. Vizbaras, M. Anders, C. Grasse, M.-C. Amann, Walter Schottky Institute (Germany)

MID-INFRARED QCLs

7953 17 **High performance quantum cascade lasers with broadband gain spectra (Invited Paper)** [7953-42]
Y. Yao, Princeton Univ. (United States); X. Wang, J.-Y. Fan, AdTech Optics, Inc. (United States); W. O. Charles, T. Tsai, J. Chen, G. Wysocki, C. F. Gmachl, Princeton Univ. (United States)

7953 1A **3.5 μm strain balanced GaInAs/AlInAs quantum cascade lasers operating at room temperature** [7953-71]
F. Xie, C. Caneau, H. P. LeBlanc, N. J. Visovsky, Corning Inc.(United States); Y. Wang, G. Wysocki, Princeton Univ. (United States); L. C. Hughes, C. Zah, Corning Inc. (United States)

HIGH POWER II

7953 1B **Performance and reliability of high power 7xx nm laser diodes (Invited Paper)** [7953-45]
L. Bao, J. Wang, M. Devito, D. Xu, M. Grimshaw, W. Dong, X. Guan, H. Huang, P. Leisher, S. Zhang, D. Wise, R. Martinsen, J. Haden, nLIGHT Corp. (United States)

7953 1C **Very high modulation efficiency two-sections tapered laser diode at 1060 nm for free space optical communications** [7953-46]
M. Ruiz, N. Michel, M. Calligaro, Y. Robert, M. Lecomte, O. Parillaud, M. Krakowski, Alcatel-Thales III-V Lab. (France); I. Esquivias, H. Odriozola, J. M. G. Tijero, Univ. Politécnica de Madrid (Spain); C. H. Kwok, R. V. Penty, I. H. White, Univ. of Cambridge (United Kingdom)

7953 1D **Compact ps-pulse laser source with free adjustable repetition rate and nJ pulse energy on microbench** [7953-47]
A. Klehr, A. Liero, T. Hoffmann, S. Schwertfeger, H. Wenzel, G. Erbert, W. Heinrich, G. Tränkle, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany)

7953 1E **Low-cost high-reliability 830nm single mode lasers for consumer electronics and CtP applications** [7953-48]
J. Boucart, E. Zibik, S. Renz, B. Sverdlov, Oclaro Switzerland AG (Switzerland); M. Kearley, D. Inder, C. Button, Oclaro PLC (United Kingdom); N. Lichtenstein, Oclaro Switzerland AG (Switzerland)

HIGH POWER III

7953 1F **Mitigation of thermal lensing effect as a brightness limitation of high-power broad area diode lasers** [7953-49]
J. G. Bai, P. Leisher, S. Zhang, S. Elim, M. Grimshaw, C. Bai, L. Bintz, D. Dawson, L. Bao, J. Wang, M. DeVito, R. Martinsen, J. Haden, nLIGHT Corp. (United States)

7953 1G **Reliable operation of 976nm high power DFB broad area diode lasers with over 60% power conversion efficiency (Invited Paper)** [7953-50]
P. Crump, C. M. Schultz, H. Wenzel, S. Knigge, O. Brox, A. Maaßdorf, F. Bugge, G. Erbert, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany)

7953 1I **A novel approach to finite-aperture tapered unstable resonator lasers** [7953-52]
M. Spreemann, H. Wenzel, B. Eppich, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany); M. Lichtner, Weierstrass Institute for Applied Analysis and Stochastics (Germany); G. Erbert, Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik (Germany)

7953 1J **Control of slow axis mode behaviour with waveguide phase structures in semiconductor broad-area lasers** [7953-53]
H.-C. Eckstein, U. D. Zeitner, K. Ahmed, Fraunhofer Institute for Applied Optics and Precision Engineering (Germany); W. Schmid, U. Strauss, OSRAM Opto Semiconductors (Germany)

MID-IR LASERS AND APPLICATIONS I

7953 1K **Recent results from broadly tunable external cavity quantum cascade lasers (Invited Paper)** [7953-54]
D. Caffey, M. B. Radunsky, V. Cook, M. Weida, P. R. Buerki, S. Crivello, T. Day, Daylight Solutions (United States)

7953 1L **Multi-watt level short wavelength quantum cascade lasers** [7953-55]
A. Lyakh, R. Maulini, A. G. Tsekoun, R. Go, C. K. N. Patel, Pranalytica, Inc. (United States)

MID-IR LASERS AND APPLICATIONS II

7953 1P **Design and operation of mid-IR integrated DBR tunable lasers** [7953-59]
L. Cheng, F.-S. Choa, Univ. of Maryland, Baltimore County (United States)

7953 1Q **Type-I GaSb based single lateral mode diode ridge lasers operating at room temperature in 3.1-3.2 μm spectral region** [7953-60]
G. Tsvid, T. Hosoda, J. Chen, G. Kipshidze, L. Shterengas, State Univ. of New York at Stony Brook (United States); C. Frez, A. Soibel, S. Forouhar, Jet Propulsion Lab. (United States); G. Belenky, State Univ. of New York at Stony Brook (United States)

7953 1R **Broad area lasers with folded-resonator geometry for integrated transverse mode selection** [7953-61]
D. Hoffmann, K. Huthmacher, C. Doering, H. Fouckhardt, Kaiserslautern Univ. of Technology (Germany)

7953 1S **Near-infrared induced negative photoconductance and its relationship with optical quenching of mid-infrared quantum cascade lasers** [7953-62]
D. Guo, F.-S. Choa, L. Cheng, X. Chen, Univ. of Maryland, Baltimore County (United States)

7953 1T **Novel mid-IR quantum cascade laser waveguide coupling techniques** [7953-63]
D. Shyu, F.-S. Choa, X. Chen, Univ. of Maryland, Baltimore County (United States); S. Trivedi, Brimrose Corp. (United States)

POSTER SESSION

7953 1W **Comparison of gain measurement techniques for 1.3μm quantum dot lasers** [7953-65]
H. Shahid, D. T. D. Childs, B. J. Stevens, R. A. Hogg, The Univ. of Sheffield (United Kingdom)

7953 1X **Optical gain in erbium lithium niobate titanium diffused waveguides** [7953-66]
G. A. Ejzak, D. W. Prather, Univ. of Delaware (United States)

7953 1Y **Controlled intermixing of multiple quantum wells for broadly tunable integrated lasers** [7953-67]
A. J. Zakariya, CREOL, The College of Optics and Photonics, Univ. of Central Florida (United States), Univ. of Central Florida (United States), and Information Technology & Communication Sector, MOI-Kuwait (Kuwait); N. Bickel, Univ. of Central Florida (United States); P. LiKamWa, CREOL, The College of Optics and Photonics, Univ. of Central Florida (United States) and Univ. of Central Florida (United States)

7953 1Z **Low threshold short cavity quantum cascade lasers** [7953-69]
X. Chen, L. Cheng, D. Guo, F.-S. Choa, T. Worchesky, Univ. of Maryland, Baltimore County (United States)

7953 20 **Thermal investigation of mid-infrared quantum cascade lasers under quasi-continuous-wave operations** [7953-70]
X. Chen, L. Cheng, D. Guo, F.-S. Choa, T. Worchesky, Univ. of Maryland, Baltimore County (United States)

Author Index

Conference Committee

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1 Low Dimensional Materials
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2 Grating Coupled
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3 Telecom/Datacom
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4 Nitrides
Michael Kneissl, Technische Universität Berlin (Germany)

5 Quantum Cascade Lasers I
Yu Yao, Princeton University (United States)

6 THz Quantum Cascade Lasers I
Mikhail A. Belkin, The University of Texas at Austin (United States)

7 THz Lasers II
Nanfang Yu, Harvard University (United States)

8 Silicon Photonics: Joint Session with Conference 7943
Haisheng Rong, Intel Corporation (United States)

9 High Power I
Paul O. Leisher, nLIGHT Corporation (United States)

10 Mid-infrared Lasers
Dan Botez, University of Wisconsin-Madison (United States)

11 Mid-infrared QCLs
Jerry R. Meyer, U.S. Naval Research Laboratory (United States)

12 High Power II
Gary A. Evans, Southern Methodist University (United States)

13 High Power III
Gary A. Evans, Southern Methodist University (United States)

14 Mid-IR Lasers and Applications I
Mariano Troccoli, AdTech Optics, Inc. (United States)

15 Mid-IR Lasers and Applications II
Stefan Menzel, Harvard University (United States)